

IRF730

Rev.H Jul.-2018

/ Descriptions

TO-220 N MOS N-CHANNEL MOSFET in a TO-220 Plastic Package.

/ Features

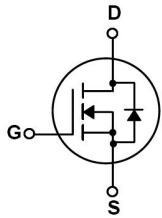
Low gate charge, low crss, fast switching.

/ Applications

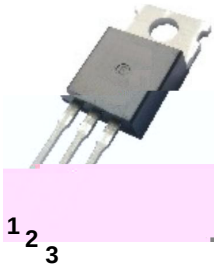
DC/DC

These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.

/ Equivalent Circuit



/ Pinning



PIN1 G

PIN 2 D

PIN 3 S

/ h_{FE} Classifications & Marking

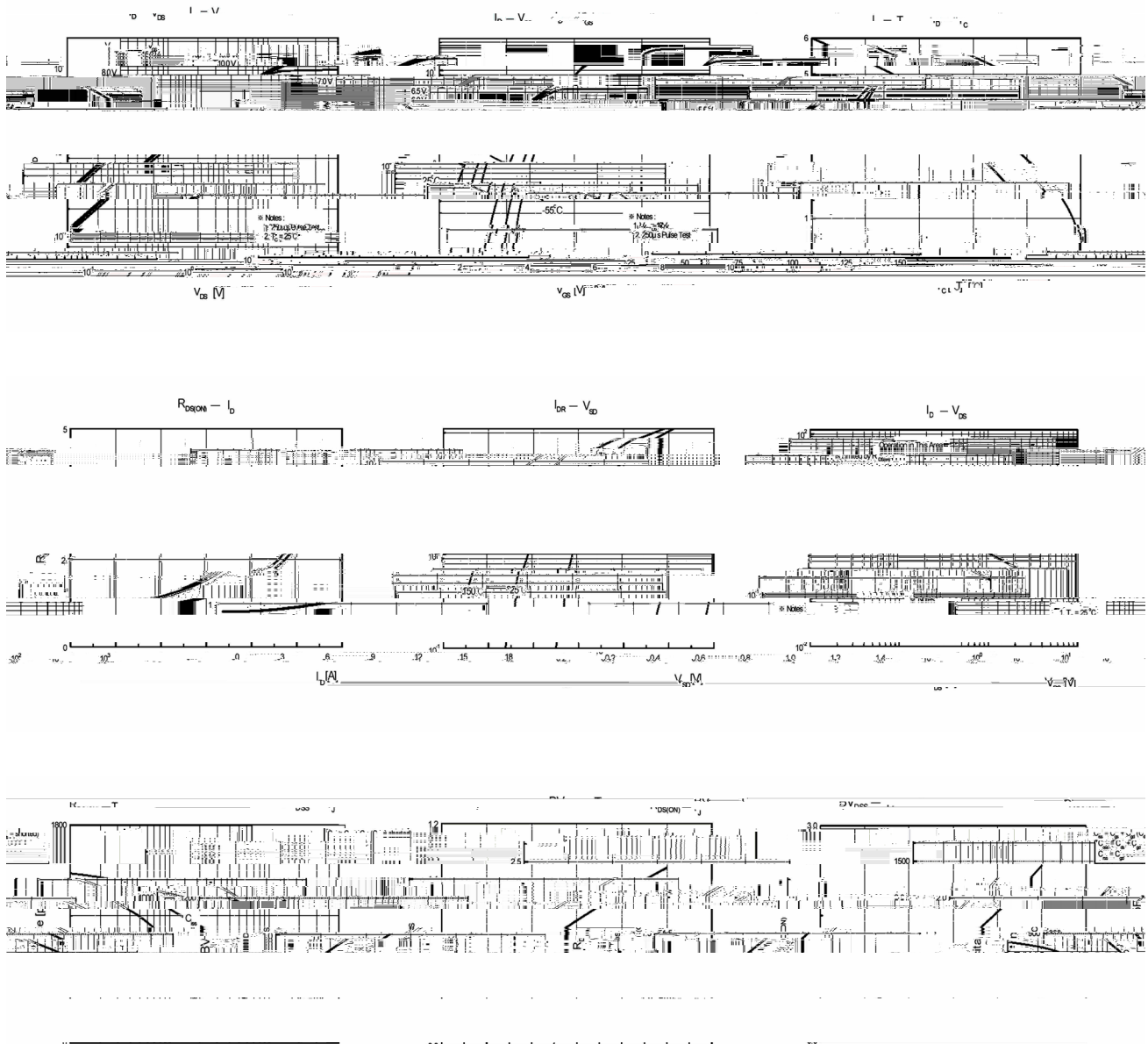
See Marking Instructions.

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Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	400	V
Drain Current	$I_D(T_c=25^\circ\text{C})$	6.0	A
	$I_D(T_c=100^\circ\text{C})$	3.6	A
Pulsed Drain Current	I_{DM}	24	A
Gate-Source Voltage	V_{GSS}	± 30	V
Avalanche Current	I_{AR}	5.5	A
Single Pulsed Avalanche Energy	E_{AS}	390	mJ
Repetitive Avalanche Energy	E_{AR}	8.75	mJ
Total Power Dissipation	$P_D(T_c=25^\circ\text{C})$	87.5	W
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	R

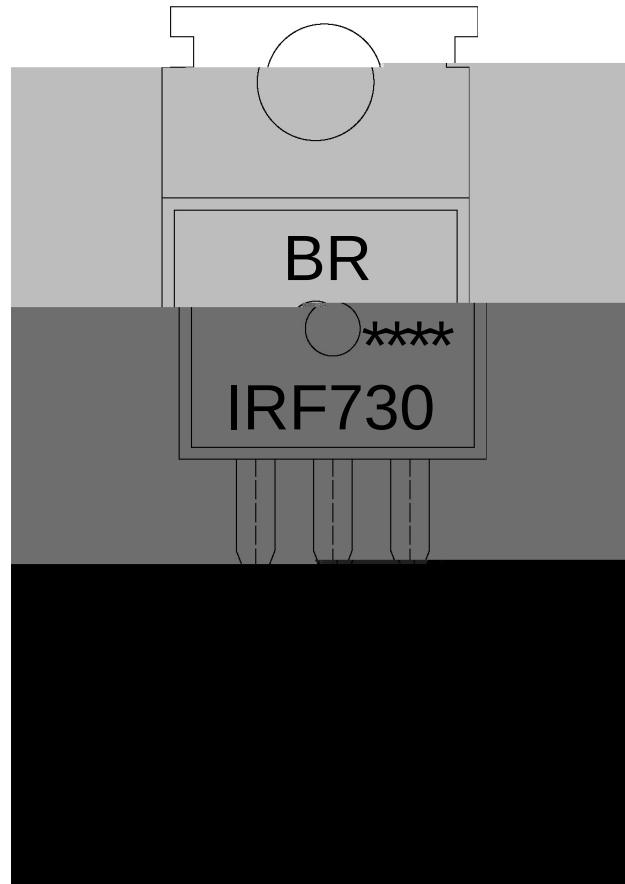
/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



BR

IRF730

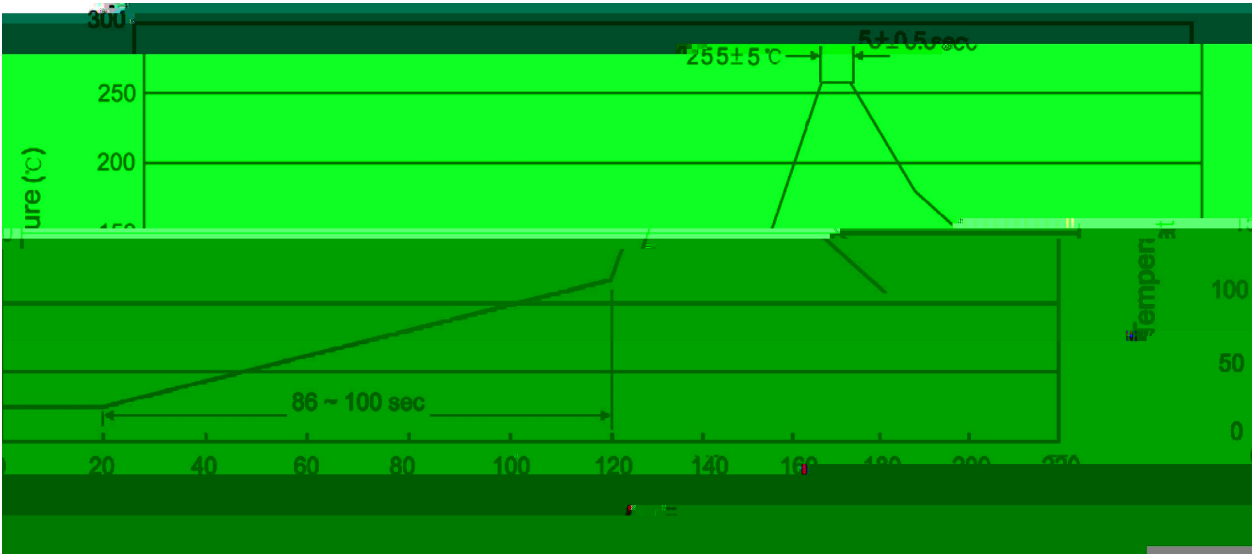
Note:

BR: Company Code

IRF730: Product Type.

****: Lot No. Code, code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- | | | | | | |
|---|-------|-----|-----------|---|--------------------------------------|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 255±5 | | 5±0.5sec; | 2.Peak Temp.:255±5 , Duration:5±0.5sec. | |
| 3 | | 2 | 10 | /sec. | 3. Cooling Speed: 2~10 /sec. |

/ Resistance to Soldering Heat Test Conditions

270±5 10±1 sec. Temp.:270±5 Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type